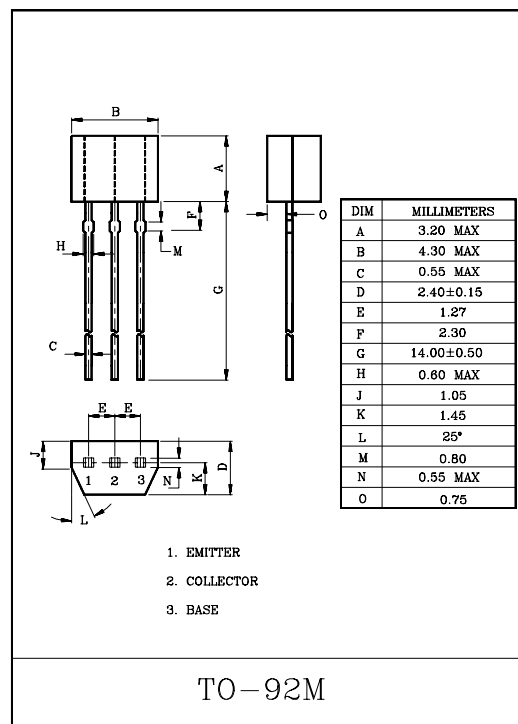
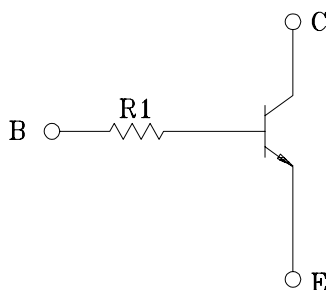


SWITCHING APPLICATION.  
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

#### FEATURES

- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.

#### EQUIVALENT CIRCUIT



#### MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	50	V
Emitter-Base Voltage	$V_{EBO}$	10	V
Collector Current	$I_C$	100	mA
Collector Power Dissipation	$P_C$	400	mW
Junction Temperature	$T_j$	150	℃
Storage Temperature Range	$T_{stg}$	-55~150	℃

# KRC110M~KRC114M

## ELECTRICAL CHARACTERISTICS(Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		$I_{CBO}$	$V_{CB}=50V, I_E=0$	–	–	100	nA
Emitter Cut-off Current		$I_{EBO}$	$V_{EB}=5V, I_C=0$	–	–	100	nA
DC Current Gain		$h_{FE}$	$V_{CE}=5V, I_C=1mA$	120	–	–	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=10mA, I_B=0.5mA$	–	0.1	0.3	V
Transition Frequency		$f_T$ *	$V_{CE}=10V, I_C=5mA$	–	250	–	MHz
Input Resistor	KRC110M	$R_i$		–	4.7	–	k $\Omega$
	KRC111M			–	10	–	
	KRC112M			–	100	–	
	KRC113M			–	22	–	
	KRC114M			–	47	–	
Switching Time	Rise Time	KRC110M	$V_O=5V$ $V_{IN}=5V$ $R_L=1k\Omega$	–	0.025	–	$\mu S$
		KRC111M		–	0.03	–	
		KRC112M		–	0.3	–	
		KRC113M		–	0.06	–	
		KRC114M		–	0.11	–	
	Storage Time	KRC110M		–	3.0	–	
		KRC111M		–	2.0	–	
		KRC112M		–	6.0	–	
		KRC113M		–	4.0	–	
		KRC114M		–	5.0	–	
	Fall Time	KRC110M		–	0.2	–	
		KRC111M		–	0.12	–	
		KRC112M		–	2.0	–	
		KRC113M		–	0.9	–	
		KRC114M		–	1.4	–	

Note : \*Characteristic of Trnsistor Only